

FIG.1

(Related Art)

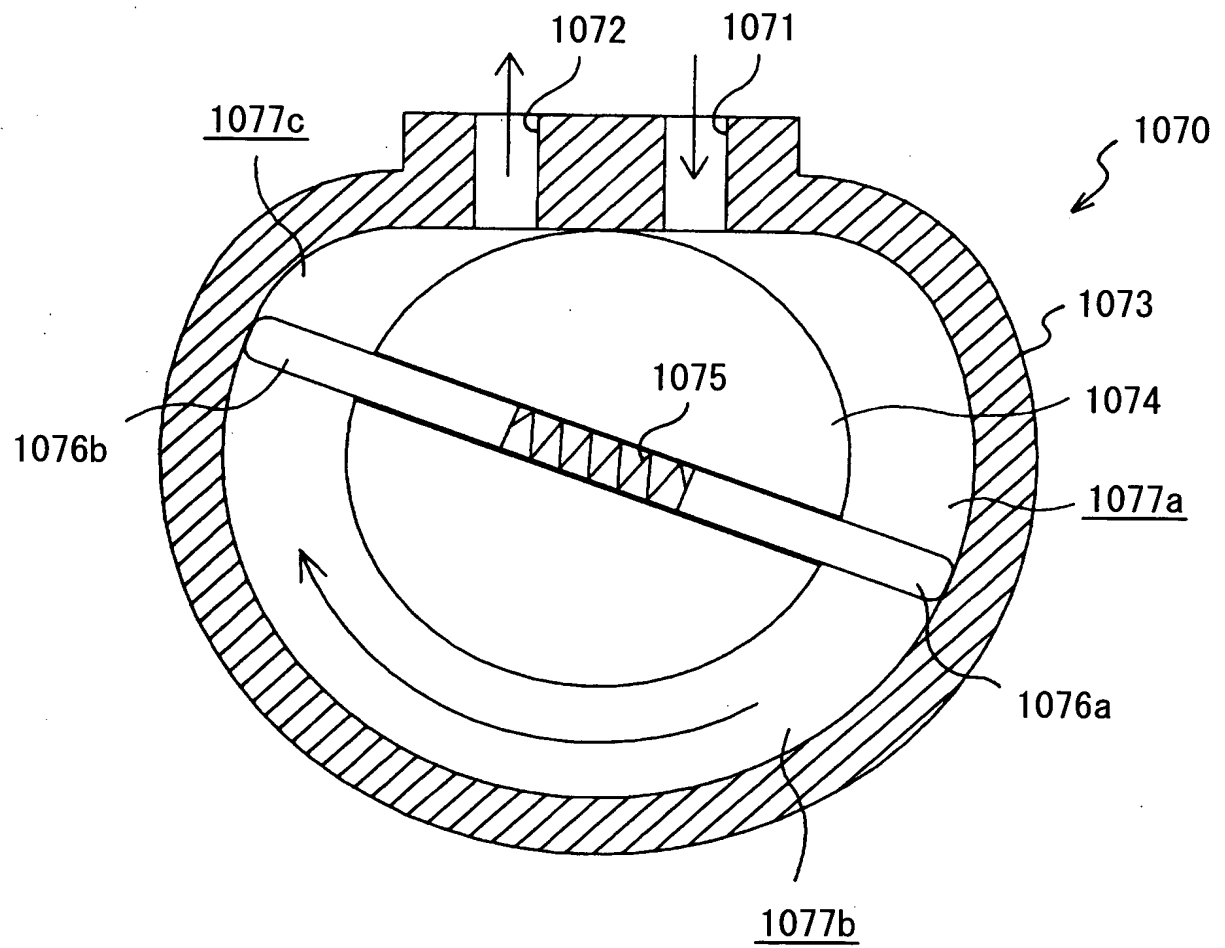


FIG.2

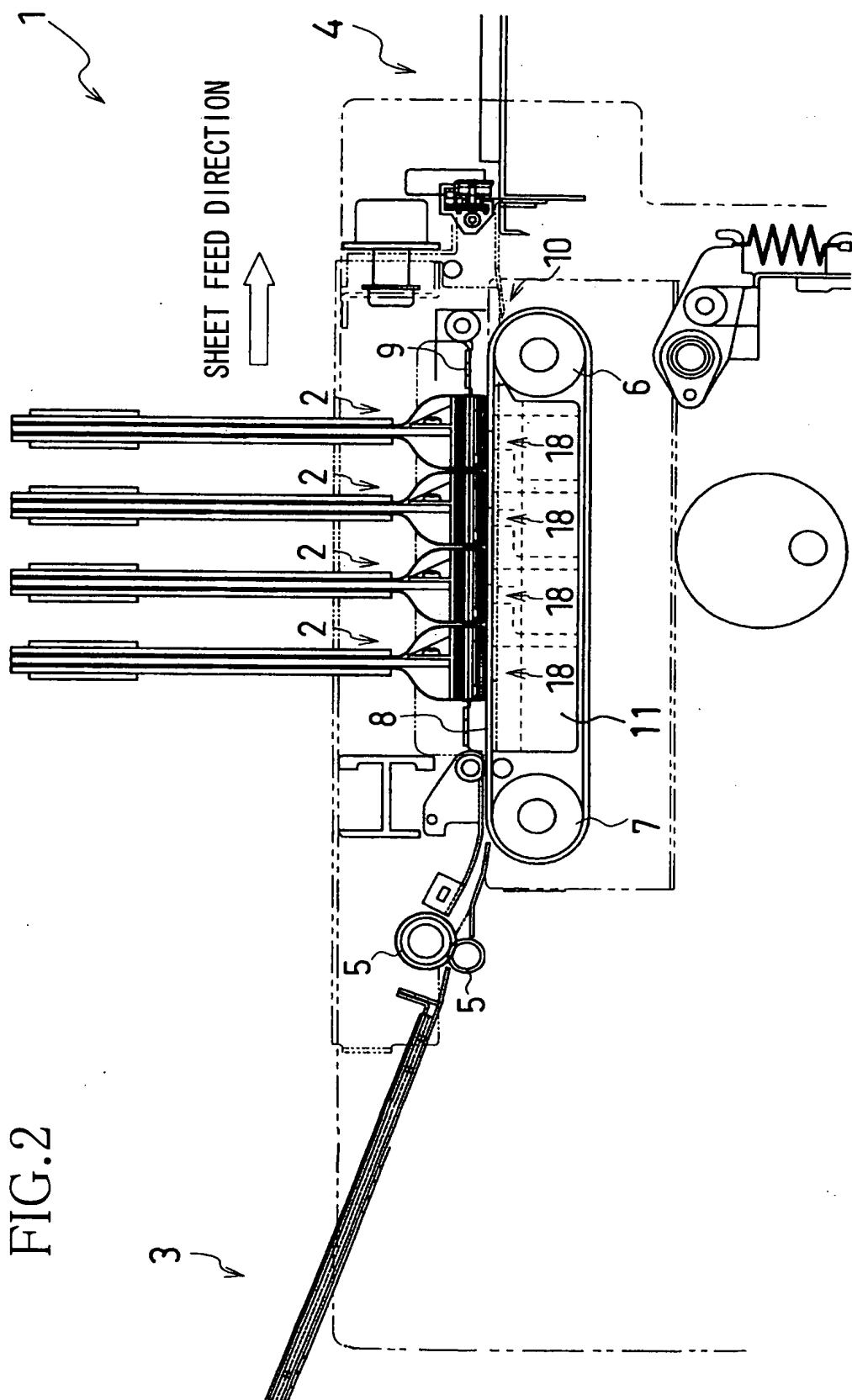


FIG. 3

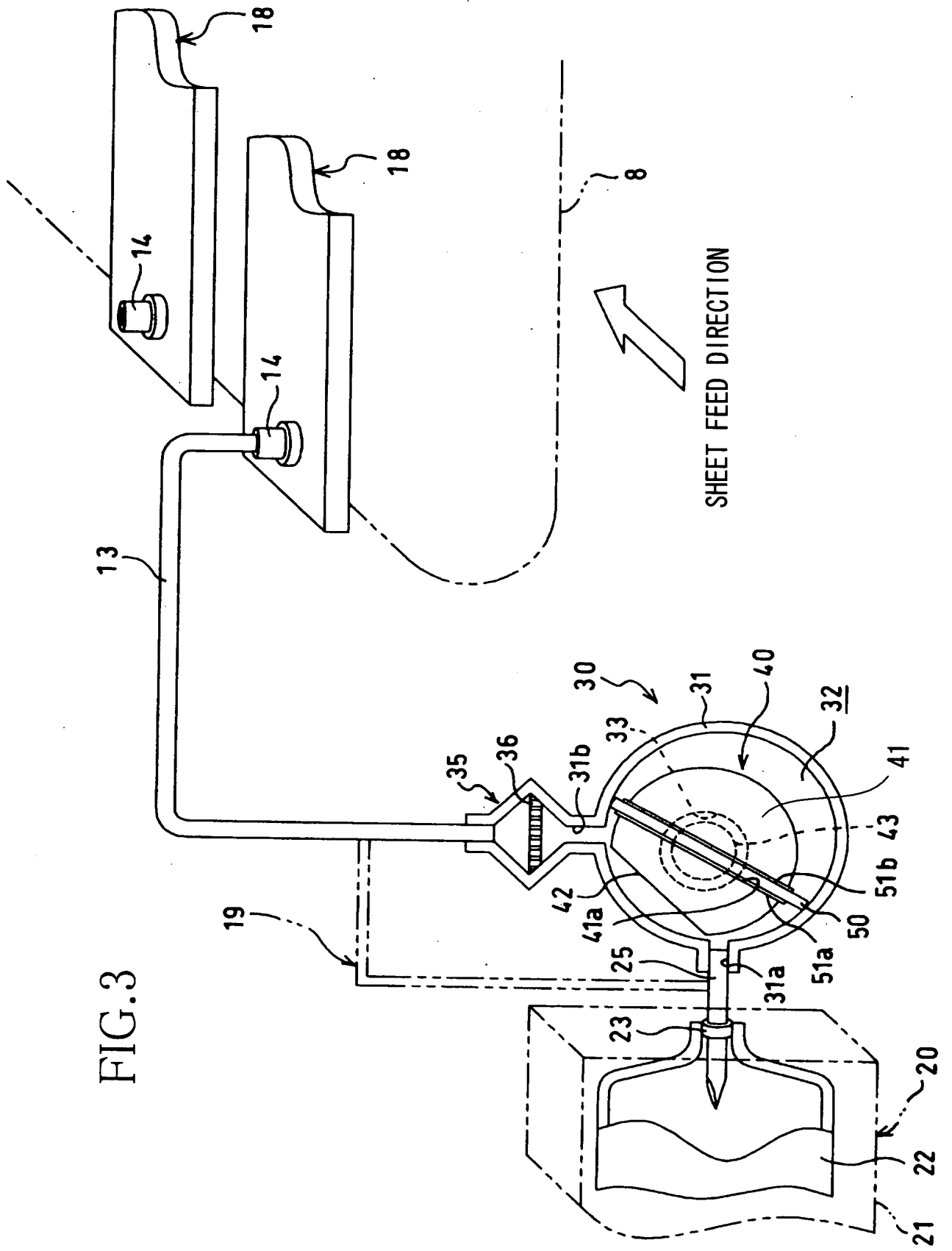


FIG. 4A

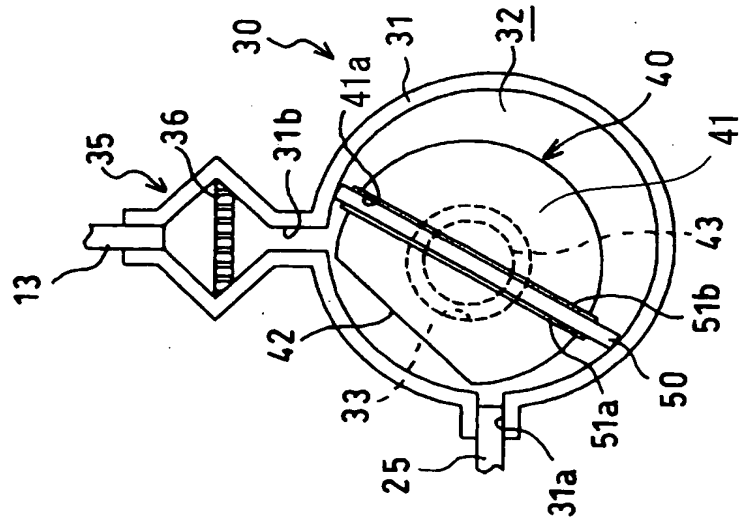


FIG. 4B

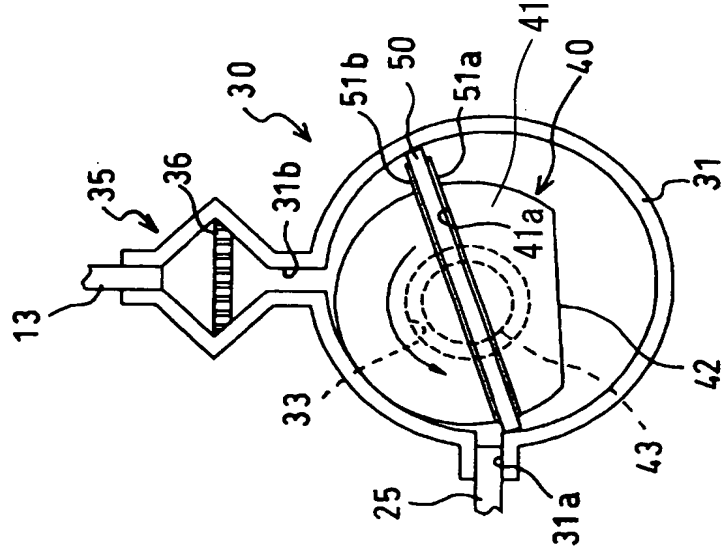


FIG. 4C

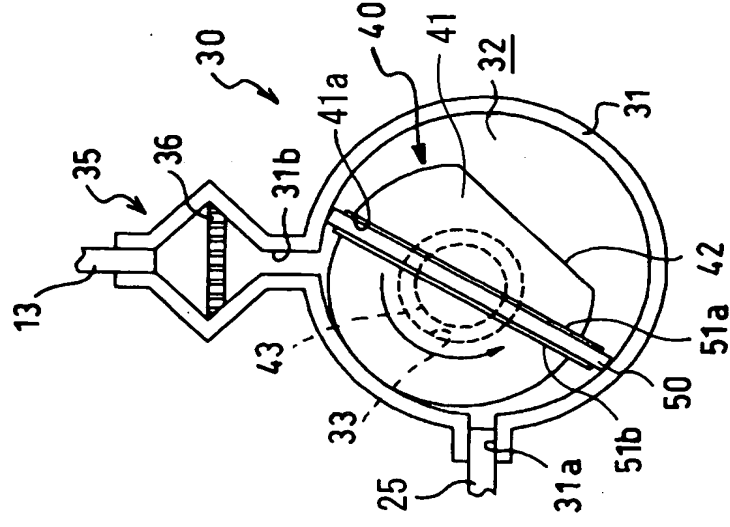


FIG. 5A

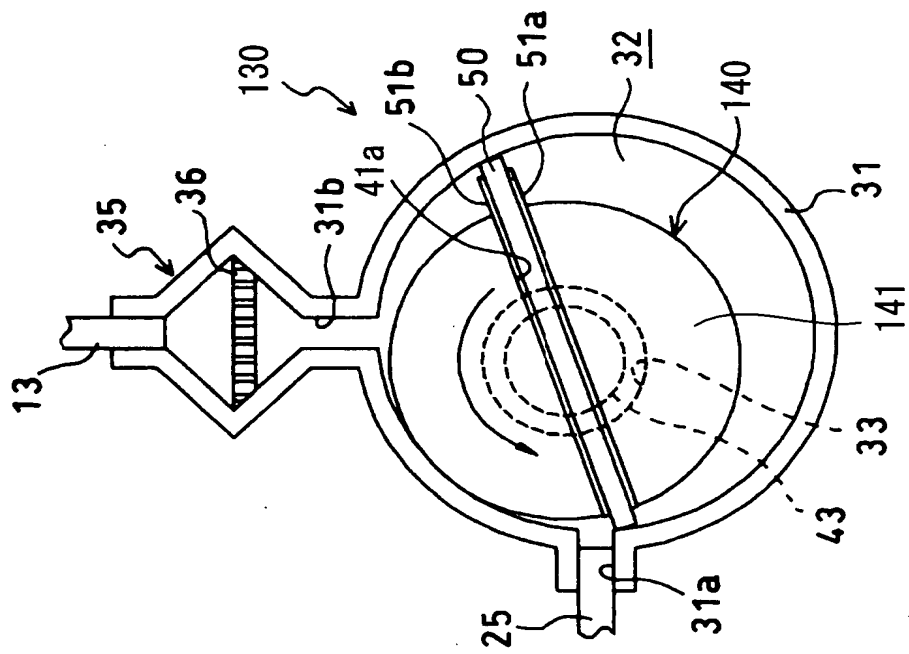


FIG. 5B

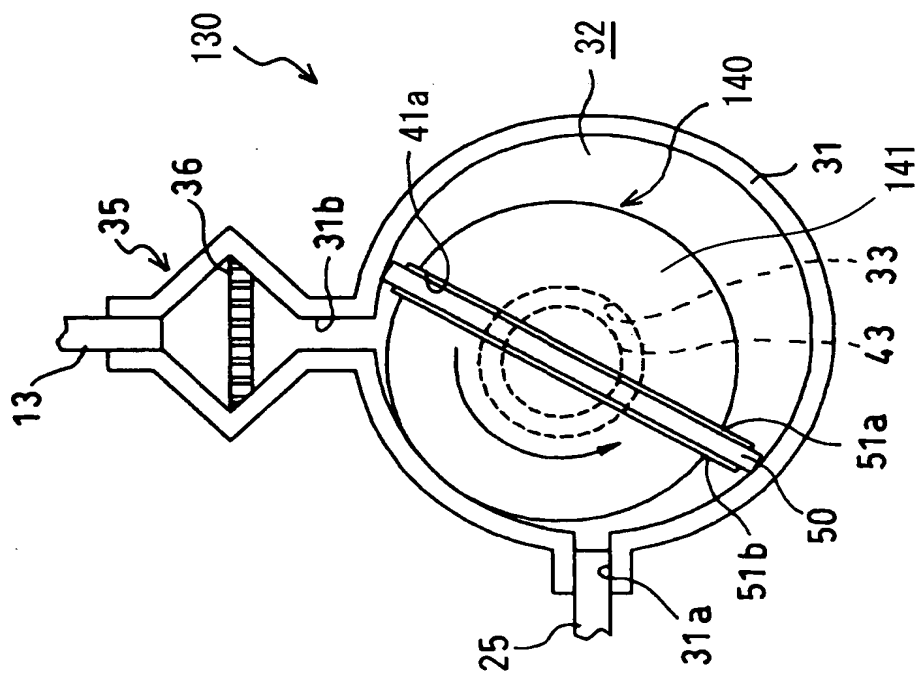


FIG. 6 is a cross-sectional view of a semiconductor device. It shows a central channel 233 surrounded by a gate stack 240. The gate stack includes a gate dielectric layer 241 and a gate electrode 242. The channel 233 is formed in a substrate 245. The device is surrounded by a passivation layer 246. Other labels include 31, 32, 41a, 51a, 51b, 247, 248, 249, and 50.

FIG. 7A

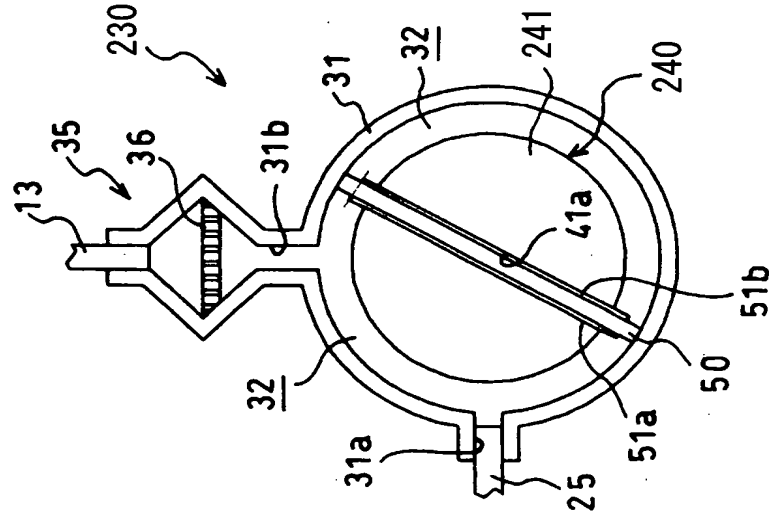


FIG. 7B

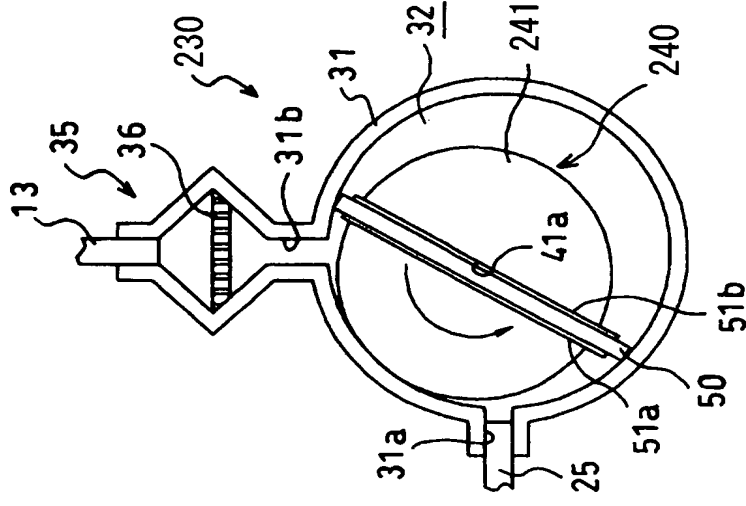


FIG. 7C

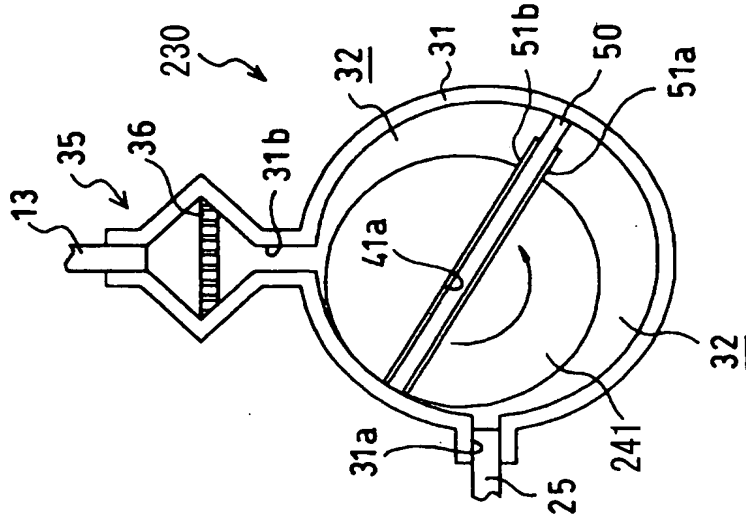


FIG. 8A

A detailed technical drawing labeled FIG. 8A. It depicts a mechanical assembly in cross-section. At the top, a large circular flange or ring is labeled 69, with an inner bore area labeled 68. A central shaft or rod, labeled 66, extends from this flange downwards. This shaft passes through a series of components: first, a small cylindrical part 61a; then, a larger circular housing or cap 61 which contains internal structures 65 and 65a. Below this housing is another component 31a, followed by a base or support structure 50 containing elements 51a and 51b. To the right, there's a vertical assembly consisting of parts 13, 35, 36, and 31b, which appears to be a valve or actuator mechanism. A bracket 330 groups parts 35, 36, and 31b. Other labels include 25, 41a, 32, 340, and 341, pointing to various surfaces and interfaces within the assembly.

[illegible]

FIG. 9A

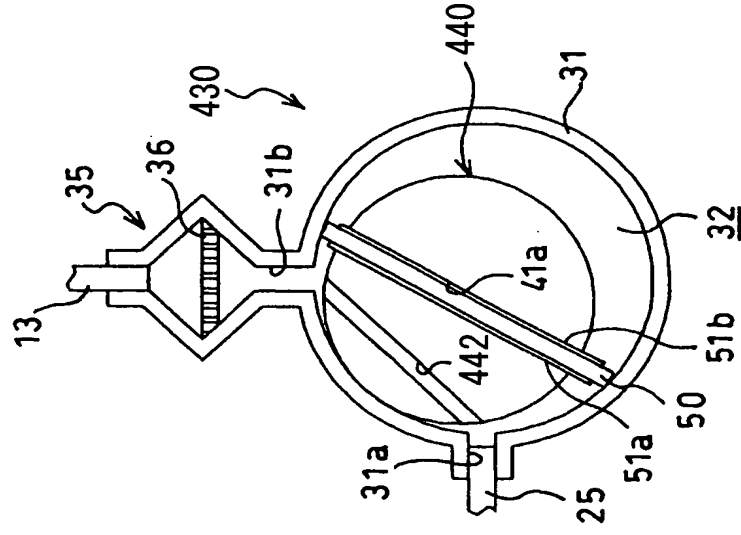


FIG. 9B

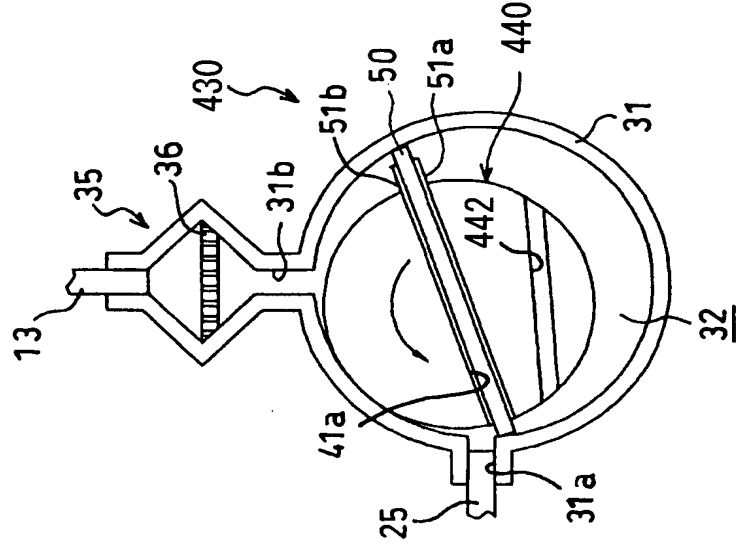


FIG. 9C

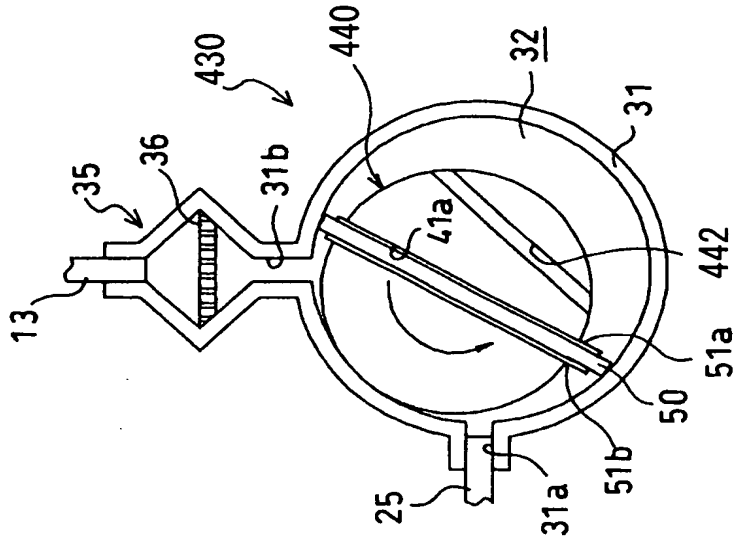
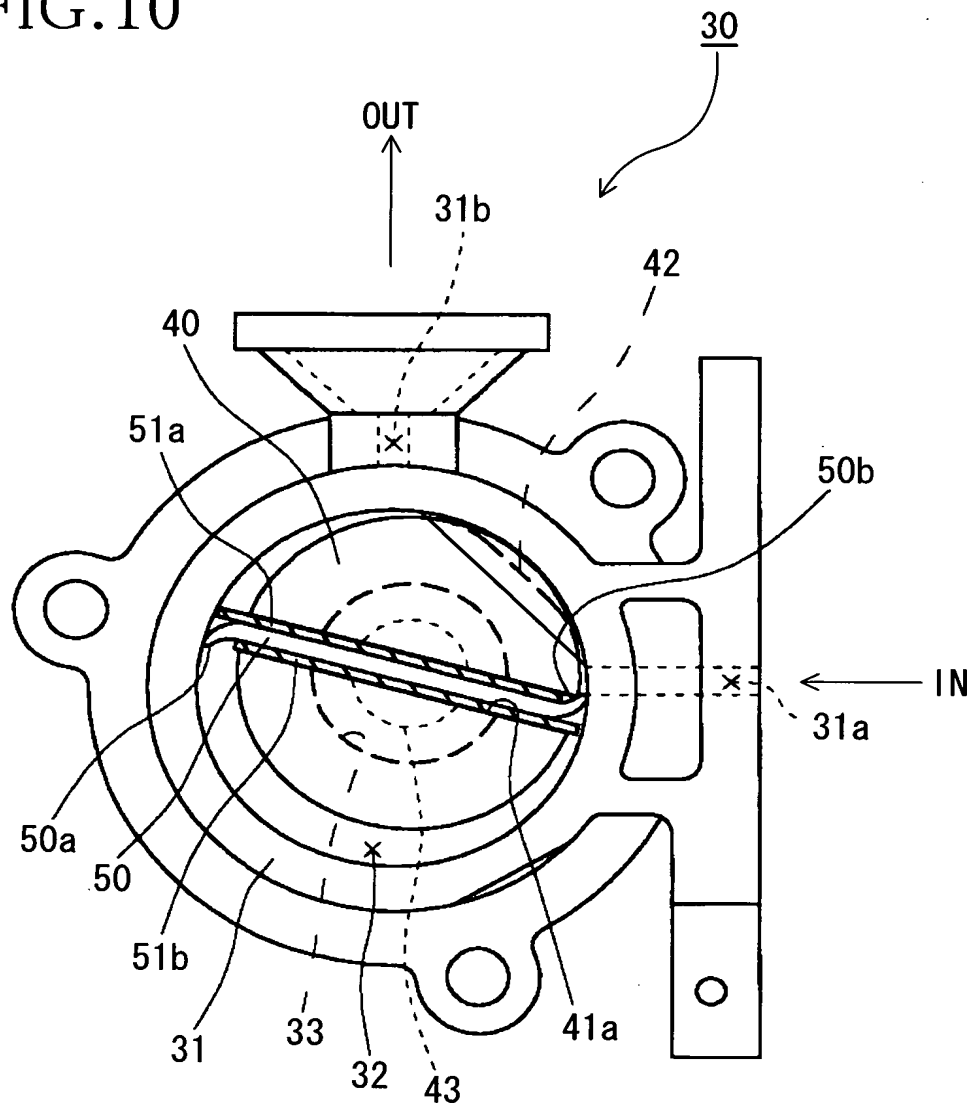


FIG.10



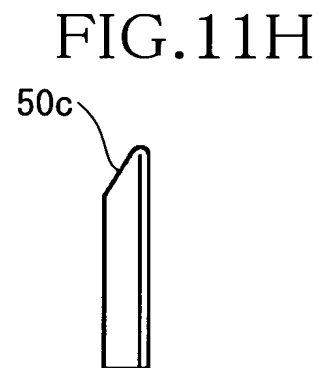
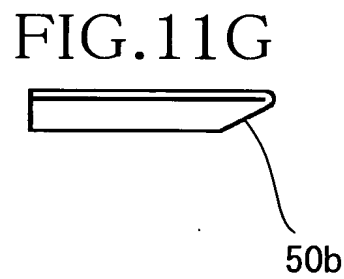
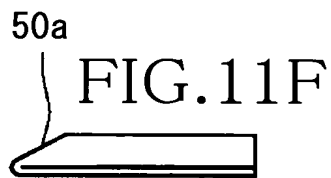
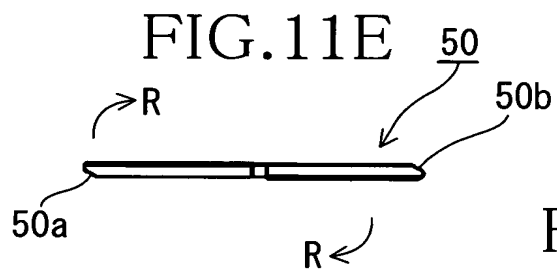
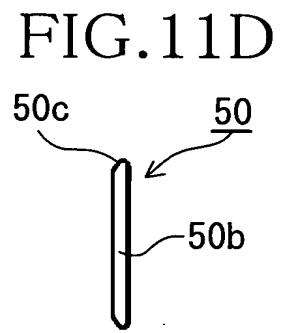
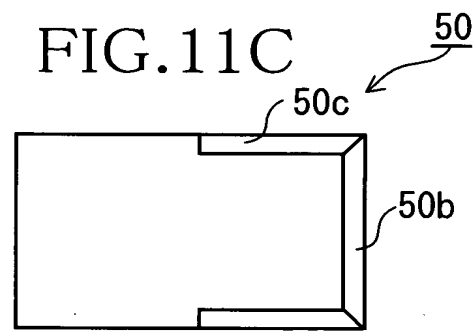
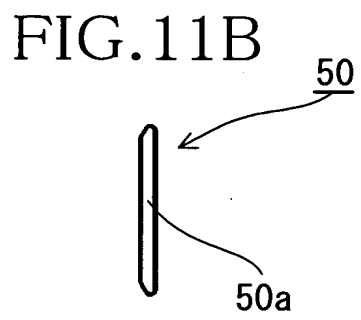


FIG.12A

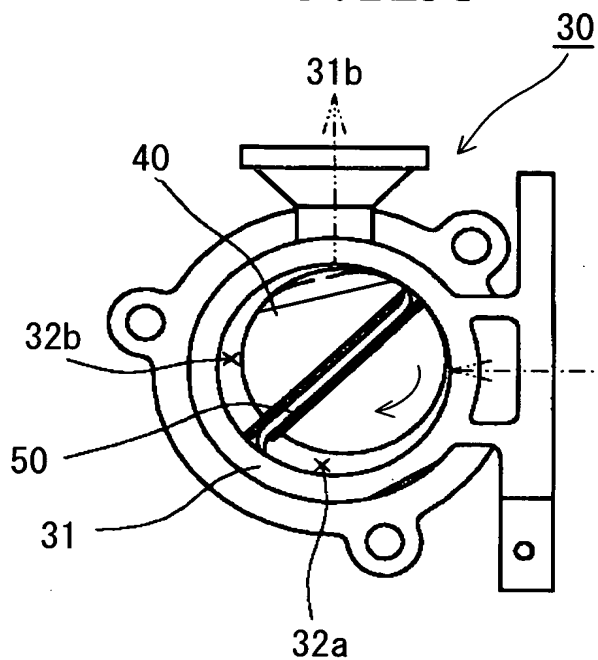


FIG.12C

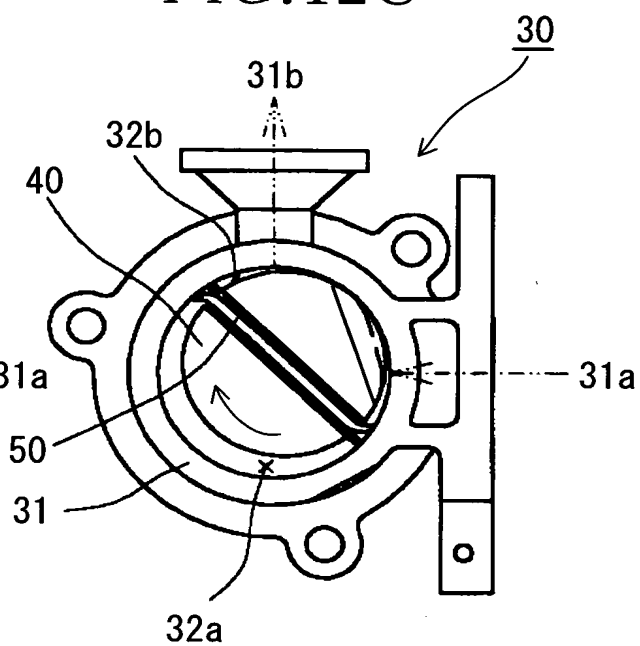


FIG.12B

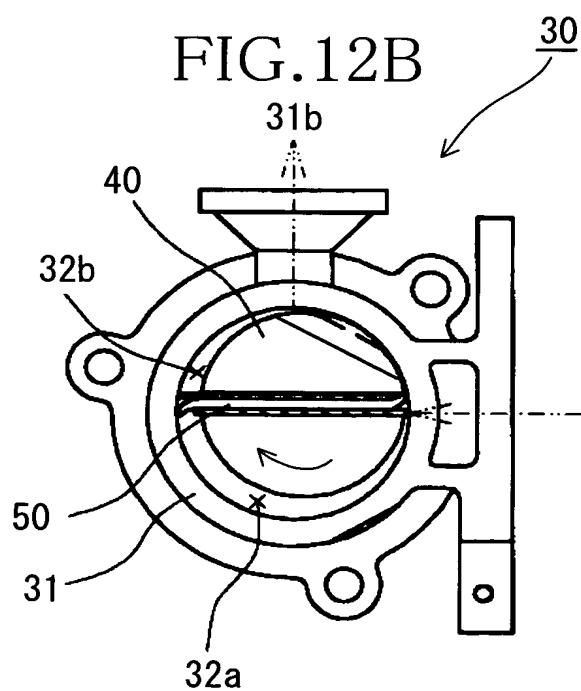


FIG.12D

